

# N-channel TrenchMOS intermediate level FET Rev. 3 — 14 October 2010

Product data sheet

#### 1. **Product profile**

#### 1.1 General description

Intermediate level gate drive N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using advanced TrenchMOS technology. This product has been designed and qualified to the appropriate AEC Q101 standard for use in high performance automotive applications.

#### 1.2 Features and benefits

- AEC Q101 compliant
- Suitable for intermediate level gate drive sources

#### 1.3 Applications

- 12 V Automotive systems
- Electric and electro-hydraulic power steering
- Motors, lamps and solenoid control

### 1.4 Quick reference data

#### Table 1 Quick reference data

- Suitable for thermally demanding environments due to 175 °C rating
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

Table 1.	QUICK reference	uata					
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	40	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; see <u>Figure 1</u>	<u>[1]</u>	-	-	100	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	-	204	W
Static cha	racteristics						
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; see <u>Figure 11</u>		-	3.05	3.6	mΩ



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Table 1.	Quick reference da	tacontinued				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Avalanche	e ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$ \begin{split} I_D &= 100 \text{ A};  \text{V}_{\text{sup}} \leq 40 \text{ V}; \\ R_{\text{GS}} &= 50  \Omega;  \text{V}_{\text{GS}} = 10 \text{ V}; \\ T_{j(\text{init})} &= 25 ^{\circ}\text{C}; \text{ unclamped} \end{split} $	-	-	368	mJ
Dynamic of	characteristics					
Q <sub>GD</sub>	gate-drain charge	$\begin{split} I_D &= 25 \text{ A};  V_{DS} = 32 \text{ V}; \\ V_{GS} &= 10 \text{ V}; \text{ see } \underline{\text{Figure 13}}; \\ \text{see } \underline{\text{Figure 14}} \end{split}$	-	42	-	nC

[1] Continuous current is limited by package.

### 2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	Drain	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT226 (I2PAK)	

### 3. Ordering information

Table 3. Ordering i	nformation		
Type number	Package		
	Name	Description	Version
BUK6E3R4-40C	I2PAK	plastic single-ended package (I2PAK); TO-262	SOT226

BUK6E3R4-40C

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### 4. Limiting values

#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Мах	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	40	V
V <sub>GS</sub>	gate-source voltage	Pulsed	<u>[1]</u>	-20	20	V
		DC	[2]	-16	16	V
I <sub>D</sub>	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V}; \text{ see } \frac{\text{Figure 1}}{\text{Figure 1}}$	[3]	-	100	А
		$T_{mb}$ = 100 °C; $V_{GS}$ = 10 V; see Figure 1	[3]	-	100	А
I <sub>DM</sub>	peak drain current	$T_{mb} = 25 \text{ °C}; t_p \le 10 \mu\text{s}; \text{ pulsed};$ see <u>Figure 3</u>		-	657	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	204	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drai	n diode					
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	<u>[3]</u>	-	100	А
I <sub>SM</sub>	peak source current	$t_p \le 10 \ \mu s$ ; pulsed; $T_{mb} = 25 \ ^{\circ}C$		-	657	А
Avalanche r	uggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$\label{eq:ld} \begin{array}{l} I_D = 100 \; A; \; V_sup \leq 40 \; V; \; R_GS = 50 \; \Omega; \\ V_GS = 10 \; V; \; T_j(init) = 25 \; ^\circ C; \; unclamped \end{array}$		-	368	mJ
E <sub>DS(AL)R</sub>	repetitive drain-source avalanche energy		<u>[4][5][6]</u>	-	-	J

[1] Accumulated pulse duration not to exceed 5mins.

[2] -16V accumulated duration not to exceed 168 hrs.

[3] Continuous current is limited by package.

[4] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

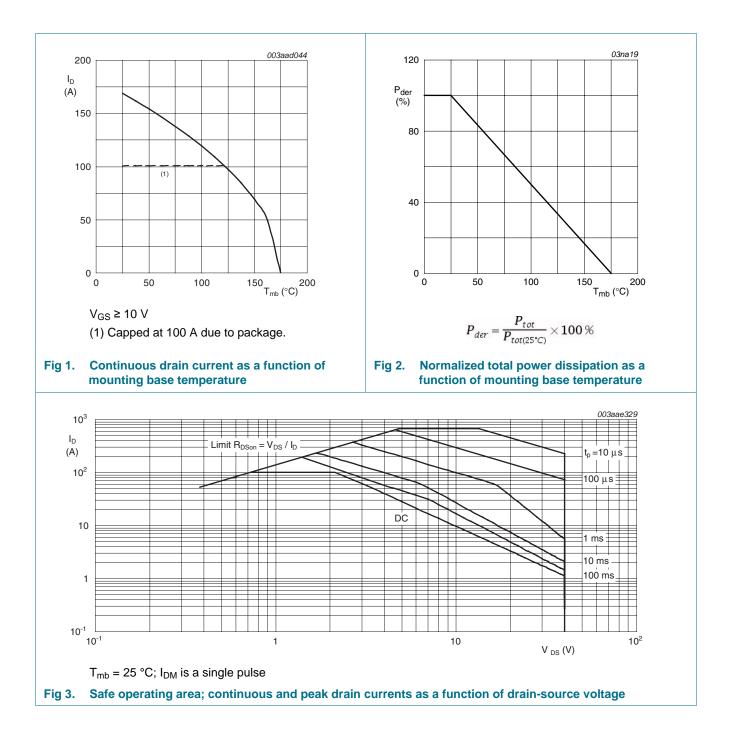
[5] Repetitive avalanche rating limited by an average junction temperature of 170 °C.

[6] Refer to application note AN10273 for further information.

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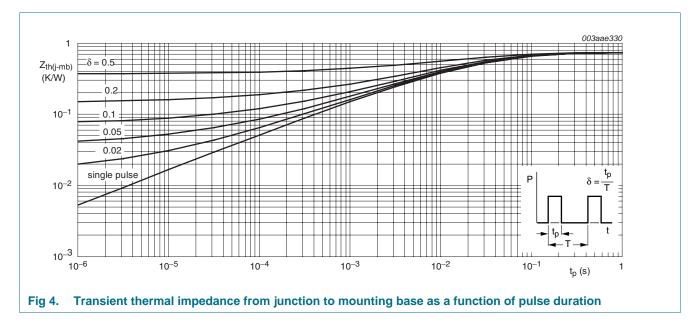
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### 5. Thermal characteristics

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	see Figure 4	-	-	0.74	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	vertical in free air	-	60	-	K/W



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### 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub>	drain-source	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	40	-	-	V
	breakdown voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^\circ C$	36	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 25 °C; see <u>Figure 9</u> ; see <u>Figure 10</u>	1.8	2.3	2.8	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = -55 °C; see <u>Figure 10</u>	-	-	3.3	V
		I <sub>D</sub> = 2.5 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 175 °C; see <u>Figure 10</u>	0.8	-	-	V
DSS	drain leakage current	$V_{DS}$ = 40 V; $V_{GS}$ = 0 V; $T_j$ = 175 °C	-	-	500	μΑ
		$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	1	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{DS} = 0 \text{ V}; \text{ V}_{GS} = 20 \text{ V}; \text{ T}_{j} = 25 \text{ °C}$	-	2	100	nA
		$V_{DS} = 0 \text{ V}; V_{GS} = -20 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 11</u>	-	3.05	3.6	mΩ
		V <sub>GS</sub> = 5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; see <u>Figure 11</u>	-	4.2	5.3	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; see <u>Figure 11</u>	-	4.5	6	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; see <u>Figure 12</u> ; see <u>Figure 11</u>	-	-	7.6	mΩ
Dynamic ch	naracteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 13</u> ; see <u>Figure 14</u>	-	125	-	nC
		$I_D = 25 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 5 \text{ V};$ see <u>Figure 13</u> ; see <u>Figure 14</u>	-	71	-	nC
Q <sub>GS</sub>	gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 10 \text{ V};$	-	23	-	nC
Q <sub>GD</sub>	gate-drain charge	see Figure 13; see Figure 14	-	42	-	nC
C <sub>iss</sub>	input capacitance	$V_{GS} = 0 \text{ V};  V_{DS} = 25 \text{ V};  \text{f} = 1 \text{ MHz};$	-	6016	8020	pF
C <sub>oss</sub>	output capacitance	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 15}{15}$	-	739	870	pF
C <sub>rss</sub>	reverse transfer capacitance		-	510	700	pF
d(on)	turn-on delay time	$V_{DS}$ = 30 V; $R_L$ = 1.2 $\Omega; ~V_{GS}$ = 10 V;	-	40	-	ns
r	rise time	$R_{G(ext)} = 10 \ \Omega$	-	87	-	ns
d(off)	turn-off delay time		-	224	-	ns
f	fall time		-	117	-	ns
-D	internal drain inductance	from drain lead 6 mm from package to centre of die; $T_j = 25 \text{ °C}$	-	4.5	-	nH
L <sub>S</sub>	internal source inductance	from source lead to source bond pad; $T_i = 25 ^{\circ}\text{C}$	-	7.5	-	nH

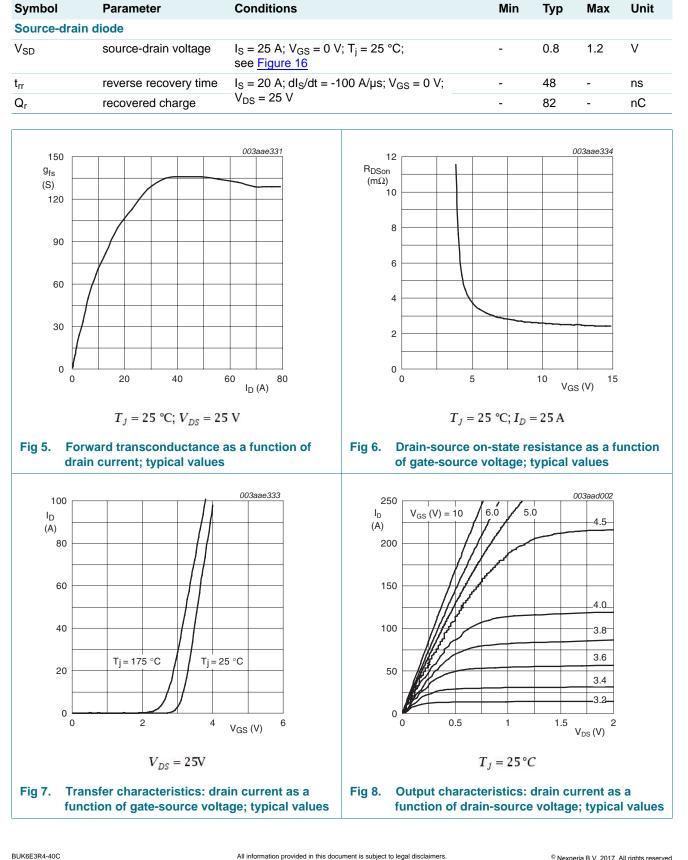
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Table 6.

Characteristics ... continued

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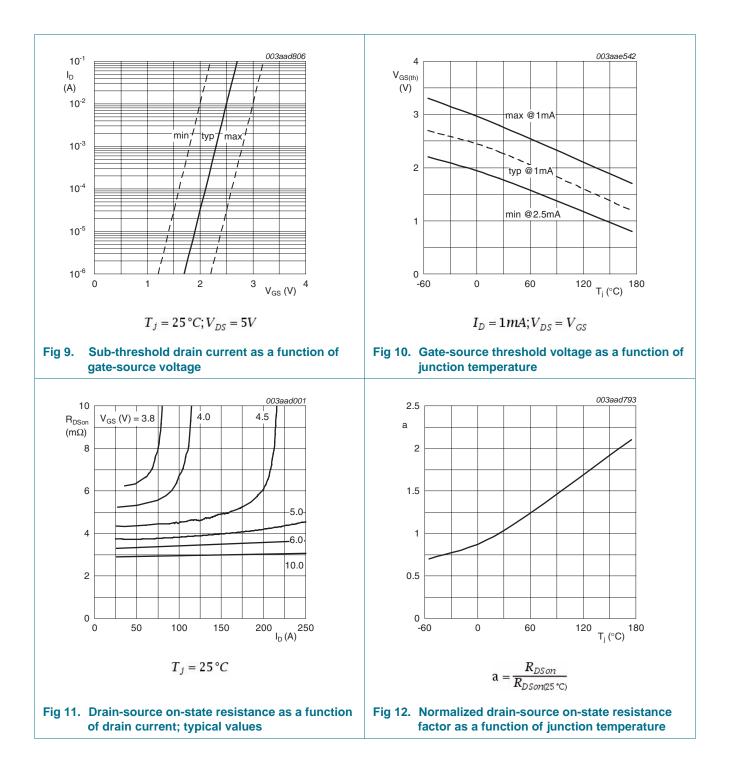


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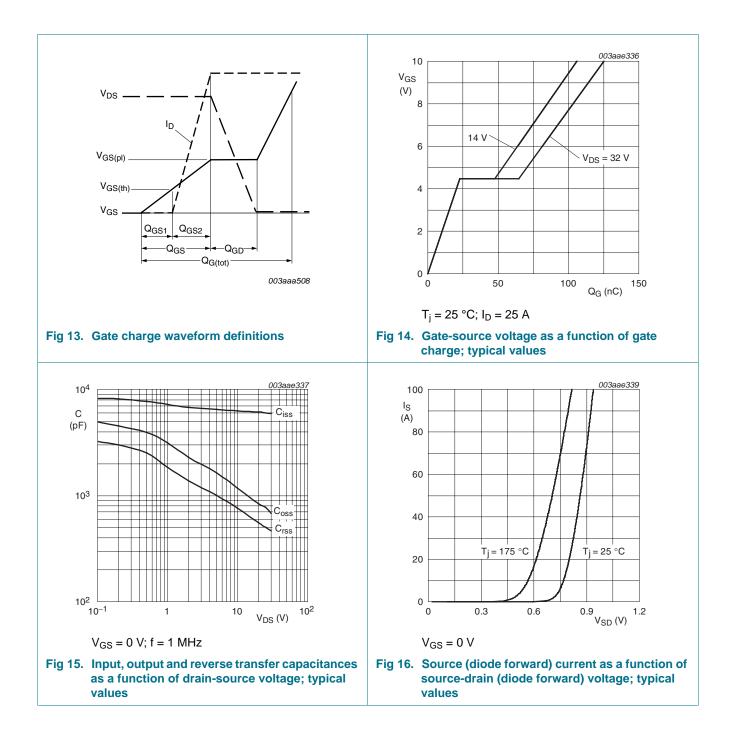


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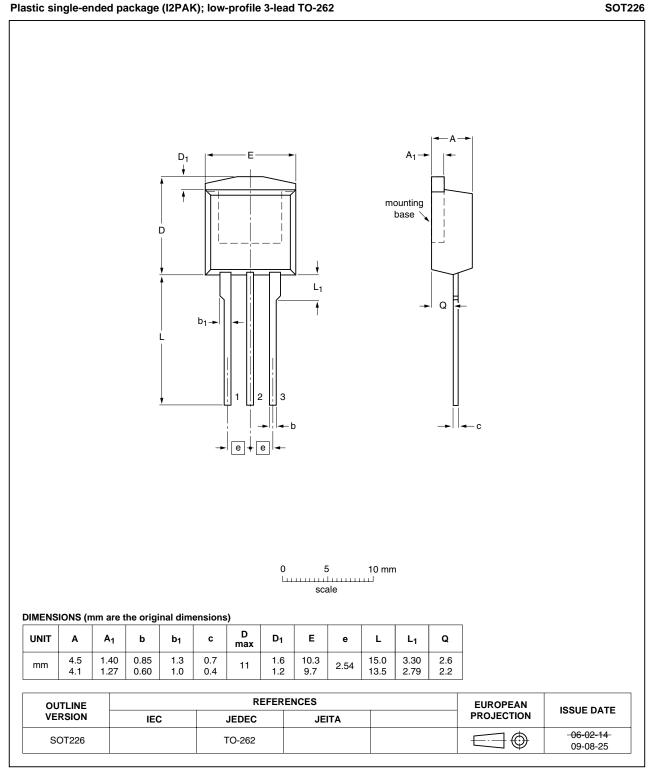
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### 7. Package outline



#### Fig 17. Package outline SOT226 (I2PAK)

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### 8. Revision history

Table 7.Revision h	nistory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK6E3R4-40C v.3	20101014	Product data sheet	-	BUK6E3R4-40C v.2
Modifications:	<ul> <li>Status change</li> </ul>	d from objective to product.		
BUK6E3R4-40C v.2	20100621	Objective data sheet	-	BUK6E3R4-40C v.1

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### 9. Legal information

#### 9.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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